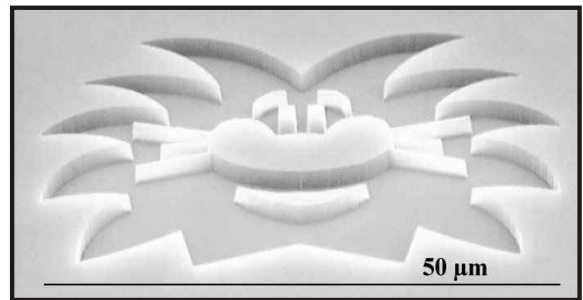
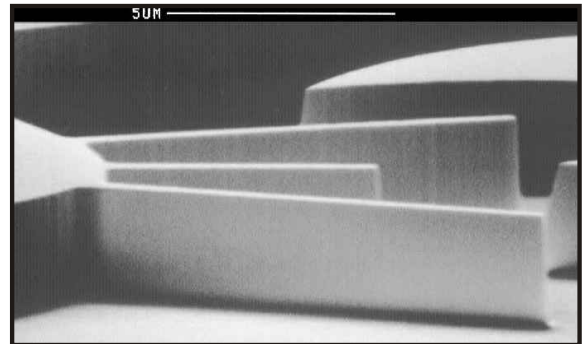
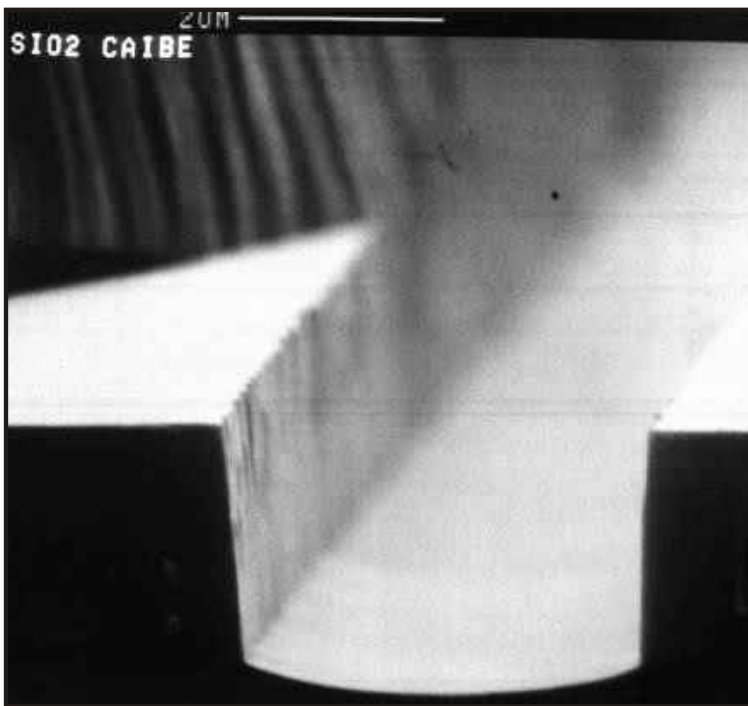


Ionfab Data

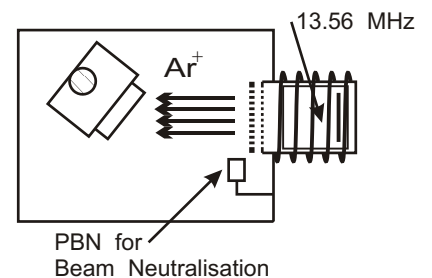
CAIBE/ RIBE of SiO₂



OPT Application Lab:
3.5 µm deep etch (85° slope at normal incidence)
with polyimide mask removed

Courtesy of Uni Jena, Angewandte Physik:
2.5 µm deep Quartz etch (RIBE)
with Cr mask (deposited by IBS)

Ionfab 300 Plus



Technology:

- Etch Mode: CAIBE, RIBE
- Rotating substrate with adjustable tilt
- Ion source: 15 cm, 13.56 MHz driven
- Ion Optics: High Current / Low Energy
- Neutralisation: filamentfree PBN

Results:

- Rate : 30 - 200 nm/min (CAIBE)
- Selectivity: > 30 : 1 to Cr (RIBE)
- Selectivity: ca. 2:1 to Polyimide(CAIBE)
- Wall Angle: adjustable
- Rate and Selectivity increase with tilt (CAIBE)